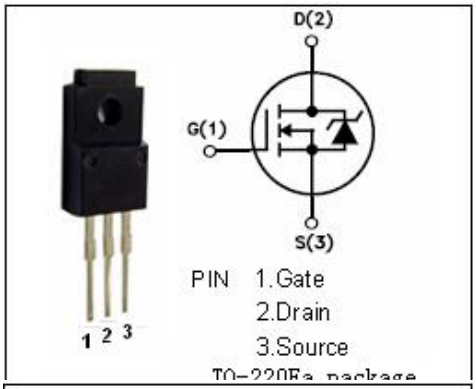
isc N-Channel MOSFET Transistor 2SK525

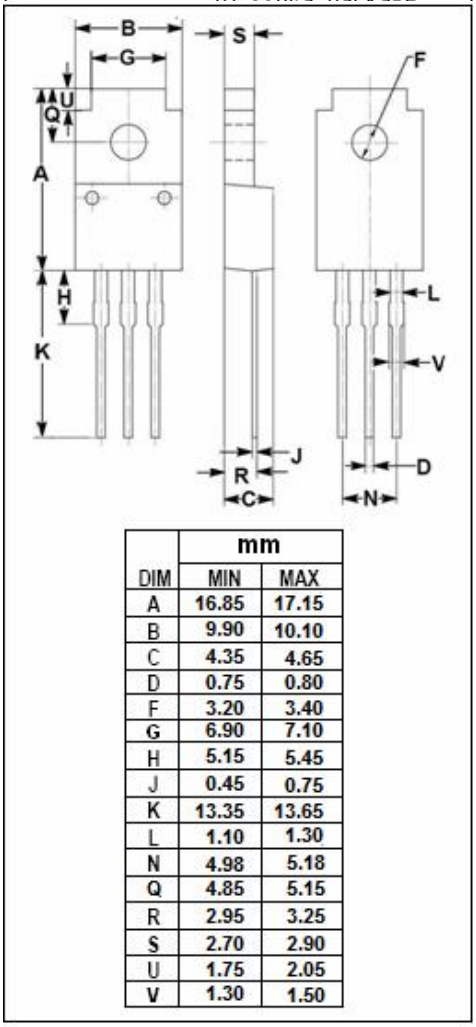
DESCRIPTION

- Drain Current –I_D=10A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=150V(Min)
- Fast Switching Speed



APPLICATIONS

- Designed especially for low voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.



DIM	mm MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	150	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	10	A
P_{tot}	Total Dissipation@TC=25℃	40	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.67	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 10mA	150			V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D= 1mA	1.5		3.5	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 10V; I_D=5A		0.2	0.28	Ω
$V_{DS(ON)}$	Drain-Source Saturation Voltage	I_F= 10A; V_{GS}=10V		2.2	3.0	V
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V; V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=150V; V_{GS}= 0			1	mA
tr	Rise time	V_{GS}=10V;I_D=5A; R_L=50Ω		75	140	ns
ton	Turn-on time			85	170	ns
tf	Fall time			55	110	ns
toff	Turn-off time			160	320	ns

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